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Docket No.: M4065.0536/P536-B
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Hongmei Wang et al.

Application No.: 10/751,443

Confirmation No.: 2565

Filed: January 6, 2004

Art Unit: 2814

For: FULLY-DEPLETED (FD) (SOI) MOSFET
ACCESS TRANSISTOR (AS AMENDED)

Examiner: C. M. D. Pizarro

AMENDMENT IN RESPONSE TO NON-FINAL OFFICE ACTION

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

In response to the Office Action dated March 21, 2005 (Paper No. 0305),
please amend the above-identified U.S. patent application as follows:

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins
on page 3 of this paper.

Remarks begin on page 5 of this paper.